

Appl. No. 09/767,918
Amendment dated: July 11, 2003
Reply to OA of: April 15, 2003

This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

Claims 1-10(canceled).

11(currently amended). An improved structure for the packaging technique of a large size FED comprising of:

an ITO conducting glass;

on the ITO conducting glass is defined to a BM layer area, a multi-phosphor layer area, and a hollow area, in which the inside of a hollow area is formed a Cr/CrO_x layer area;

said areas are coated with an Al layer;

an Al layer is coated with an AlO_x layer;

a spacer is fixed on an AlO_x layer of the hollow area; and

a lower plate is fixed on the spacer.

12(currently amended). An improved structure for the packaging technique of a large size FED of claim 11, wherein said method of forming an Al layer is an evaporation, and the thickness is around 1000-3000 angstroms.

13(currently amended). An improved structure for the packaging technique of a large size FED of claim 11, wherein the temperature of ~~the~~ a sintering process ~~of for~~ for the phosphor layer is around 500-560 °C.

14(currently amended). An improved structure for the packaging technique of a large size FED of claim 11, wherein the thickness of the AlO_x layer is around 50-200 angstroms.

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15(currently amended). An improved structure for the packaging technique of a large size FED of claim 11, wherein said the thickness of the Cr/CrO_x layer is around 1000-3000 angstroms.

16(currently amended). An improved structure for the packaging technique of a large size FED of claim 11, wherein said spacer is form as a column structure, and the height of the spacer is about 1.1 mm.

17(currently amended). An improved structure for the packaging technique of a large size FED of claim 11, wherein there is a plurality of bonding areas between the spacer and a AlO_x layer.

18(currently amended). An improved structure for the packaging technique of a large size FED of claim 11, wherein said method of fixing the spacer is an anodic bonding technique.

19(currently amended). An improved structure for the packaging technique of a large size FED of claim 11, wherein the voltage of fixing the spacer is 1.00-1.50 V/μm.

20(currently amended). An improved structure for the packaging technique of a large size FED of claim 11, wherein the temperature of fixing the substrate glass of the spacer is 200-300 °C.
